2N7002KW

N-Channel MOSFET

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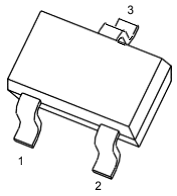
$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
60 V	5K@10V	340mA
	5.3K@4.5V	

SOT-323



1. GATE
2. SOURCE
3. DRAIN

FEATURE

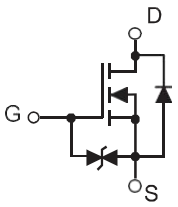
- z Highdensity celldesign for Low $R_{DS(on)}$
- z Voltagecontrolled smallsignal switch
- z Rugged andreliable
- z High saturation current capability
- z ESD protected

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING

Equivalent Circuit



MOSFET MAXIMUM RATINGS (T_a=25Я unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	340	mA
I_{DM}	Pulsed Drain Current(note1)	800	mA
P_D	Power Dissipation	0.2	W
T_j	Junction Temperature	150	Я
T_{stg}	Storage Temperature	-55~+150	Я
$R_{ŞJA}$	Thermal Resistance from Junction to Ambient	625	Я/W

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25 Š unless otherwise specified

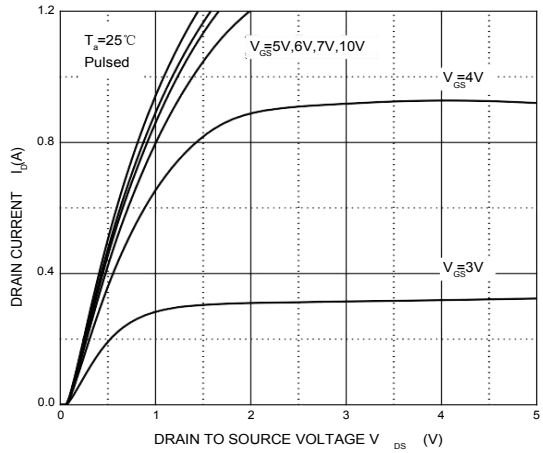
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	60			V
GateThreshold Voltage (note 2)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =1mA	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =48V,V_{GS} = 0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±10	μA
Drain-Source On-Resistance (note 2)	$R_{DS(on)}$	V_{GS} =4.5V, I_D =200mA		1.1	5.3	Ω
		V_{GS} =10V, I_D =500mA		0.9	5	Ω
DYNAMIC PARAMETERS (note 3)						
Input Capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
SWITCHING PARAMETERS(note 3)						
Turn-on Delay Time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=50V, R_G=50ὠ			10	ns
Turn-off Delay Time	$t_{d(off)}$	R_{GS}=50ὠ, R_L=250ὠ			15	ns
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA,V_R=25V, dIs/dt=-100A/us		30		ns
Recovered Charge	Qr	V_{GS}=0V,I_S=300mA,V_R=25V dIs/dt=-100A/us		30		nC
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	Igs=1mA(Open Drain)	21.5		30	V
DRAIN-SOURCE DIODE						
Diode Forward Voltage(note 2)	V_{SD}	I_S=300mA, V_{GS} = 0V			1.5	V
Continuous Diode Forward Current	I_S				0.2	A
Pulsed Diode Forward Current(note1)	I_{SM}				0.53	A

Notes :

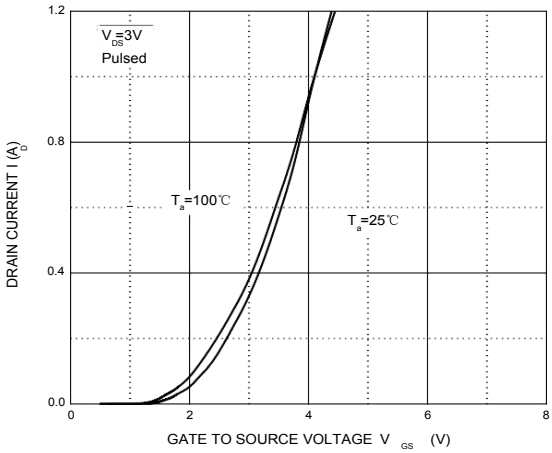
1. Repetitive rating→Pluse width limited by junction temperature.
2. Pulse Test : Pulse width”300μs, duty cycle”2%.
3. Guaranteed by design, not subject to production testing.

Typical Characteristics

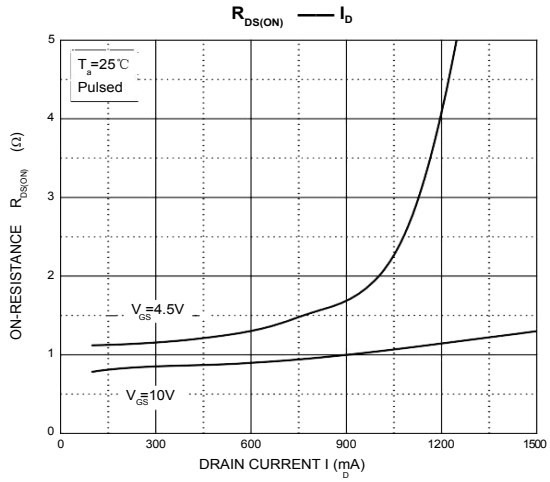
Output Characteristics



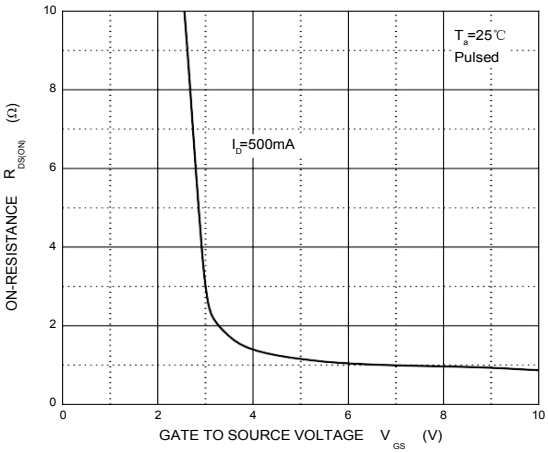
Transfer Characteristics



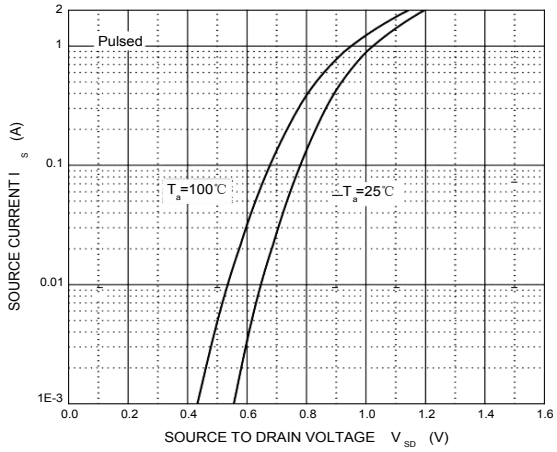
$R_{DS(ON)}$ —— I_D



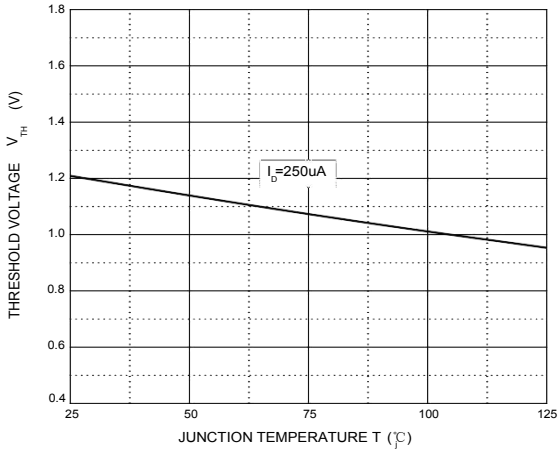
$R_{DS(ON)}$ —— V_{GS}



I_S —— V_{SD}

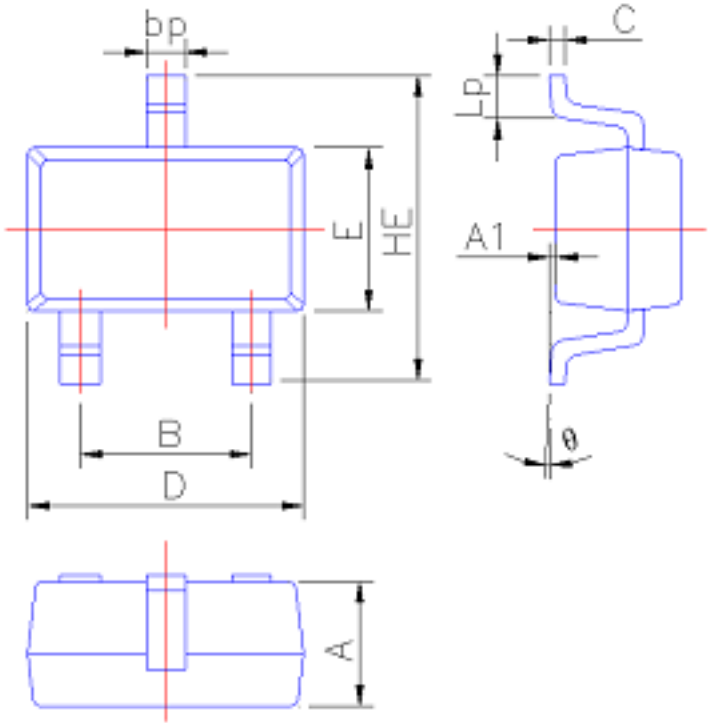


Threshold Voltage



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-323**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°